

**Please add the following new claims:**

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Q' --13. An input/output protection device in accordance with claim 3, wherein the third diffusion layer has a depth equal to or more than that of the fourth diffusion layer.

14. An input/output protection device in accordance with claim 2, wherein a lateral, bipolar transistor including the first diffusion layer as a collector, the second and third diffusion layers as an emitter, and the region of the first conduction type or the fourth diffusion layer as a base is put to operation.

15. An input/output protection device in accordance with claim 3, wherein a lateral, bipolar transistor including the first diffusion layer as a collector, the second and third diffusion layers as an emitter, and the region of the first conduction type or the fourth diffusion layer as a base is put to operation.

16. An input/output protection device in accordance with claim 4, wherein a lateral, bipolar transistor including the first diffusion layer as a collector, the second and third diffusion layers as an emitter, and the region of the first conduction type or the fourth diffusion layer as a base is put to operation.

17. An input/output protection device in accordance with claim 2, wherein the first and second diffusion layers are isolated from each other by a device separating isolation layer on a surface of the semiconductor substrate.

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